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FAN54005 USB-Compliant Single-Cell Li-Ion Switching Charger with USB-OTG Boost Regulator

Features

- Fully Integrated, High-Efficiency Charger for Single-Cell Li-Ion and Li-Polymer Battery Packs
- Charge Voltage Accuracy: ±0.5% at 25°C

±1% from 0 to 125°C

- ±5% Input Current Regulation Accuracy
- ±5% Charge Current Regulation Accuracy
- 20 V Absolute Maximum Input Voltage
- 6 V Maximum Input Operating Voltage
- 1.45 A Maximum Charge Rate
- Programmable through High-Speed I²C Interface (3.4 Mb/s) with Fast Mode Plus Compatibility
 - Input Current
 - Fast-Charge / Termination Current
 - Charger Voltage
 - Termination Enable
- 3 MHz Synchronous Buck PWM Controller with Wide Duty Cycle Range
- Small Footprint 1 μH External Inductor
- Safety Timer with Reset Control
- 1.8 V Regulated Output from VBUS for Auxiliary Circuits
- Dynamic Input Voltage Control Automatically Reduces Charging Current with Weak Input Sources
- Low Reverse Leakage to Prevent Battery Drain to VBUS
- 5 V, 500 mA Boost Mode for USB OTG for 3.0 V to 4.5 V Battery Input
- Available in a 1.96 x 1.87 mm, 20-bump, 0.4 mm Pitch WLCSP Package

Applications

- Cell Phones, Smart Phones, PDAs
- Tablet, Portable Media Players
- Gaming Device, Digital Cameras

Description

The FAN54005 combines a highly integrated switch-mode charger, to minimize single-cell Lithium-ion (Li-ion) charging time from a USB power source, and a boost regulator to power a USB peripheral from the battery.

The charging parameters and operating modes are programmable through an I²C Interface that operates up to 3.4 Mbps. The charger and boost regulator circuits switch at 3 MHz to minimize the size of external passive components.

The FAN54005 provides battery charging in three phases: conditioning, constant current and constant voltage.

To ensure USB compliance and minimize charging time, the input current limit can be changed through the I²C interface by the host processor. Charge termination is determined by a programmable minimum current level. A safety timer with reset control provides a safety backup for the I²C host. Charge status is reported to the host through the I²C port.

The integrated circuit (IC) automatically restarts the charge cycle when the battery falls below an internal threshold. If the input source is removed, the IC enters a high-impedance mode, preventing leakage from the battery to the input. Charge current is reduced when the die temperature reaches 120°C, protecting the device and PCB from damage.

The FAN54005 can operate as a boost regulator on command from the system. The boost regulator includes a soft-start that limits inrush current from the battery and uses the same external components used for charging the battery.

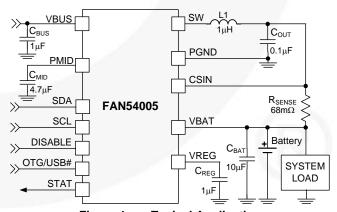


Figure 1. Typical Application

Ordering Information

Part Number	Temperature Range	Package	PN Bits: IC_INFO[4:2]	Packing Method
FAN54005UCX	-40 to 85°C	20-Bump, Wafer-Level Chip-Scale Package (WLCSP), 0.4 mm Pitch, 1.96 x 1.87 mm	101	Tape and Reel

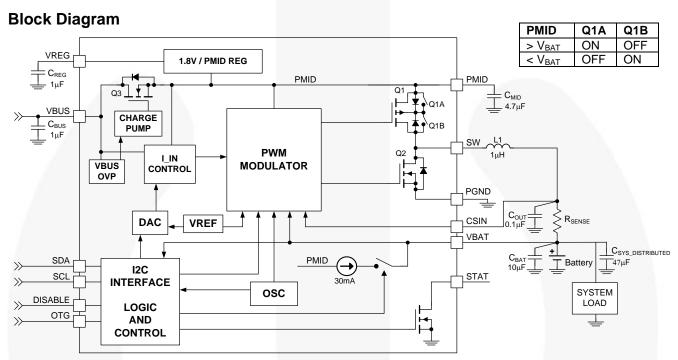


Figure 2. IC and System Block Diagram

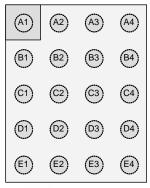
Table 1. Recommended External Components

	•				
Component	Description	Vendor	Parameter	Тур.	Unit
L1	1 μH ±20%, 4.0 A, 33 mΩ, 2016	Semco CIGT201610EH1R0M	L	1.0	μН
C_{BAT}	10 μF, 20%, 6.3 V, X5R, 0603	Murata: GRM188R60J106M TDK: C1608X5R0J106M	С	10	μF
C_{MID}	4.7 μF, 10%, 10 V, X5R, 0603	Murata: GRM188R61A475K TDK: C1608X5R1A475K	C ⁽¹⁾	4.7	μF
C_{BUS}	1.0 μF, 10%, 25 V, X5R, 0603	Murata: GRM188R61E105K TDK: C1608X5R1E105M	С	1.0	μF
C_REG	1.0 μF, 10%, 10 V, X5R, 0402	Murata: GRM155R61A105K TDK: C1005X5R1A105K	С	1.0	μF
C _{OUT}	0.1 μF, 10%, 16 V, X7R, 0402	Murata: GRM155R71C104K TDK: C1005X7R1C104K	С	0.1	μF
C _{SYS_DISTRIBUTED} (2)	n/a	n/a	С	47	μF

Notes:

- 1. A 10 V rating is sufficient for C_{MID} because PMID is protected from over-voltage surges on VBUS by Q3 (Figure 2).
- 2. A minimum 47 µF of distributed capacitance on SYS is required for proper operation of the FAN54005.

Pin Configuration



(A4) (A3) (A2) (A1) (B3) (B2) (B1) (C4) (C3) (C2) (C1) (D4) (D3) (D2) (D1) (E4) (E3) (E2) (E1)

Top View

Bottom View

Figure 3. WLCSP-20 Pin Assignments

Pin Definitions

Pin#	Name	Description
A1, A2	VBUS	Charger Input Voltage and USB-OTG output voltage. Bypass with a 1 μF capacitor to PGND.
А3	NC	No Connect. No external connection is made between this pin and the IC's internal circuitry.
A4	SCL	I ² C Interface Serial Clock. This pin should not be left floating.
B1-B3	PMID	Power Input Voltage . Power input to the charger regulator, bypass point for the input current sense, and high-voltage input switch. Bypass with a minimum of 4.7 μ F, 6.3 V capacitor to PGND.
B4	SDA	I ² C Interface Serial Data. This pin should not be left floating.
C1-C3	SW	Switching Node. Connect to output inductor.
C4	STAT	Status. Open-drain output indicating charge status. The IC pulls this pin LOW when charging.
D1-D3	PGND	Power Ground . Power return for gate drive and power transistors. The connection from this pin to the bottom of C _{MID} should be as short as possible.
D4	OTG	On-The-Go. On VBUS Power-On Reset (POR), this pin sets the input current limit for t _{15MIN} charging. Also, the OTG pin enables the boost regulator in conjunction with OTG_EN and OTG_PL bits (See Table 15)
E1	CSIN	Current-Sense Input. Connect to the sense resistor in series with the battery. The IC uses this node to sense current into the battery. Bypass this pin close to R_{SENSE} with a 0.1 μ F capacitor to PGND.
E2	DISABLE	Charge Disable . If this pin is HIGH, charging is disabled. When LOW, charging is controlled by the I ² C registers. When this pin is HIGH, the 15-minute timer is reset. This pin does not affect the 32-second timer.
E3	VREG	Regulator Output. Connect to a 1 μ F capacitor to PGND. This pin provides regulated 1.8 V and can supply up to 2mA of DC load current.
E4	VBAT	Battery Voltage. Connect to the positive (+) terminal of the battery pack and close to R _{SENSE} .

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Par	ameter		Min.	Max.	Unit	
	Vous VRUS Voltage			-0.7		V	
V _{BUS}	VBUS Voltage Puls	sed, 100 ms Max	imum Non-Repetitive	-1.0	20.0	V	
V _{STAT}	STAT Voltage			-0.3	16.0	V	
V	PMID Voltage				7.0	V	
Vı	SW, CSIN, VBAT, DISABLE Voltage			-0.3	7.0	V	
Vo	Voltage on Other Pins			-0.3	6.5 ⁽³⁾	V	
dV _{BUS}	Maximum V _{BUS} Slope above 5.5 V when Boost or Charger are Active			4	V/μs		
dV _{BUS}	Negative VBUS Slew Rate during VBU	JS Short Circuit,	T _A ≤ 60°C		4	\// a	
dt	$C_{\text{MID}} \leq 4.7 \ \mu\text{F}$ (See VBUS Short While	Charging)	T _A ≥ 60°C		2	V/μs	
ESD	Electrostatic Discharge Protection Level		Human Body Model per JESD22-A114	2000		V	
E9D			Charged Device Model per JESD22-C101	1000		V	
TJ	Junction Temperature			-40	+150	°C	
T _{STG}	Storage Temperature			-65	+150	°C	
T _L	Lead Soldering Temperature, 10 Seco	nds			+260	°C	

Note:

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter Parameter		Max.	Unit
V_{BUS}	Supply Voltage		6	V
$V_{BAT(MAX)}$	Maximum Battery Voltage when Boost enabled		4.5	V
T _A	T _A Ambient Temperature		+85	°C
TJ	Junction Temperature (See Thermal Regulation and Protection section)	-30	+120	°C

Thermal Properties

Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 2s2p boards in accordance to JEDEC standard JESD51. Special attention must be paid not to exceed junction temperature $T_{J(max)}$ at a given ambient temperature T_A . For measured data, see Thermal Regulation and Protection.

Symbol	Symbol Parameter		Unit	
θ_{JA}	θ _{JA} Junction-to-Ambient Thermal Resistance			
θ_{JB}	Junction-to-PCB Thermal Resistance	20	°C/W	

Lesser of 6.5 V or V_I + 0.3 V.

Electrical Specifications

Unless otherwise specified: according to the circuit of Figure 1; recommended operating temperature range for T_J and T_A ; $V_{BUS}=5.0 \text{ V}$; HZ_MODE ; $QPA_MODE=0$; $QPA_MODE=$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Power Su	pplies					
		V _{BUS} > V _{IN(MIN)1} , PWM Switching		10		mA
I _{VBUS}	VBUS Current	V _{BUS} > V _{IN(MIN)1} ; PWM Enabled, Not Switching (Battery OVP Condition); I_IN Setting=100 mA		2.5		mA
		0°C < T _J < 85°C, HZ_MODE=1, 32S Mode		63	90	μА
I_{LKG}	VBAT to VBUS Leakage Current	0°C < T _J < 85°C, HZ_MODE=1, V _{BAT} =4.2 V, V _{BUS} =0 V		0.2	5.0	μА
	Battery Discharge Current in	0°C < T _J < 85°C, HZ_MODE=1, V _{BAT} =4.2 V			10	
I _{BAT}	High-Impedance Mode	DISABLE=1, 0°C < T _J < 85°C, V _{BAT} =4.2 V			10	μA
Charger V	/oltage Regulation		1			
	Charge Voltage Range		3.5		4.4	
V_{OREG}	Charge Voltage Accuracy	T _A =25°C	-0.5%		+0.5%	V
		T _J =0 to 125°C	-1%		+1%	Ī
Charging	Current Regulation					
	Output Charge Current Range	$V_{SHORT} < V_{BAT} < V_{OREG}, R_{SENSE} = 68 \text{ m}\Omega$	550		1450	mA
I _{OCHARGE}	Charge Current Accuracy Across R _{SENSE}	20 mV ≤ [V _{CSIN} – V _{BAT}] ≤ 40 mV	92	97	102	%
		$[V_{CSIN} - V_{BAT}] > 40 \text{ mV}$	94	97	100	%
Weak Bat	tery Detection					
ļ.	Weak Battery Threshold Range		3.4		3.7	V
V_{LOWV}	Weak Battery Threshold Accuracy		-5		+5	%
ķī.	Weak Battery Deglitch Time	Rising Voltage		30		ms
Logic Lev	vels: DISABLE, SDA, SCL, OTG		- 7			
V_{IH}	High-Level Input Voltage		1.05			V
V_{IL}	Low-Level Input Voltage				0.4	V
I _{IN}	Input Bias Current	Input Tied to GND or V _{BUS}		0.01	1.00	μА
Charge Te	ermination Detection					
	Termination Current Range	$V_{BAT} > V_{OREG} - V_{RCH}, R_{SENSE}=68 \text{ m}\Omega$	50		400	mA
	T : :: 0 :: A	[V _{CSIN} – V _{BAT}] from 3 mV to 20 mV	-25		+25	0,
I _{TERM}	Termination Current Accuracy	[V _{CSIN} – V _{BAT}] from 20 mV to 40 mV	-5	-	+5	%
	Termination Current Deglitch Time			30		ms
1.8 V Line	ear Regulator					
V_{REG}	1.8 V Regulator Output	I _{REG} from 0 to 2 mA	1.7	1.8	1.9	V
Input Pow	ver Source Detection				ı	
V _{IN(MIN)1}	VBUS Input Voltage Rising	To Initiate and Pass VBUS Validation		4.29	4.42	V
V _{IN(MIN)2}	Minimum VBUS During Charge	During Charging		3.71	3.94	V
	VBUS Validation Time			30	t	+

Electrical Specifications

Unless otherwise specified: according to the circuit of Figure 1; recommended operating temperature range for T_J and T_A ; $V_{BUS}=5.0 \text{ V}$; HZ_MODE ; $QPA_MODE=0$; $QPA_MODE=$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Dynamic I	Input Voltage Control (V _{BUS})				ı	1
V _{SP}	DIVC Accuracy		-3		+3	%
Input Curi	rent Limit				•	
	Innut Current Limit Threshold	I _{INLIM} Set to 100 mA	88	93	98	A
I _{INLIM}	Input Current Limit Threshold	I _{INLIM} Set to 500 mA	450	475	500	⊢ mA
V _{REF} Bias	Generator					
\/	Bias Regulator Voltage	$V_{BUS} > V_{IN(MIN)1}$			6.5	V
V_{REF}	Short-Circuit Current Limit			20		mA
Battery Re	echarge Threshold					
\/	Recharge Threshold	Below V _{OREG}	100	120	150	mV
V_{RCH}	Deglitch Time	V _{BAT} Falling Below V _{RCH} Threshold		130		ms
STAT Out	put		lu .			
V _{STAT(OL)}	STAT Output Low	I _{STAT} =10 mA	1		0.4	V
I _{STAT(OH)}	STAT High Leakage Current	V _{STAT} =5 V	No.		1	μΑ
Battery De	etection				h.	
I _{DETECT}	Battery Detection Current before Charge Done (Sink Current) ⁽⁴⁾	Begins after Termination Detected and		-0.80		mA
t _{DETECT}	Battery Detection Time	V _{BAT} ≤ V _{OREG} -V _{RCH}		262		ms
Sleep Cor	mparator					
V _{SLP}	Sleep-Mode Entry Threshold, V _{BUS} – V _{BAT}	2.3 V ≤ V _{BAT} ≤ V _{OREG} , V _{BUS} Falling	0	0.04	0.10	V
t _{SLP_EXIT}	Deglitch Time for VBUS Rising Above V _{BAT} by V _{SLP}	Rising Voltage		30		ms
Power Sw	ritches (See Figure 2)					
	Q3 On Resistance (VBUS to PMID)	I _{INLIM} =500 mA		180	250	
R _{DS(ON)}	Q1 On Resistance (PMID to SW)			130	225	mΩ
	Q2 On Resistance (SW to GND)		7/	150	225	
Charger P	WM Modulator		- 4			
f_{SW}	Oscillator Frequency		2.7	3.0	3.3	MHz
D _{MAX}	Maximum Duty Cycle				100	%
D _{MIN}	Minimum Duty Cycle	- 24		0		%
I _{SYNC}	Synchronous to Non- Synchronous Current Cut-Off Threshold ⁽⁵⁾	Low-Side MOSFET (Q2) Cycle-by- Cycle Current Limit		140		mA
Boost Mo	de Operation (OPA_MODE=1, HZ	MODE=0)			100	
V	Boost Output Voltage at VBUS	$2.5~\text{V} < \text{V}_{\text{BAT}} < 4.5~\text{V},~\text{I}_{\text{LOAD}}$ from 0 to 200 mA	4.80	5.07	5.17	V
V _{BOOST}	Boost Output Voltage at VBOS	$3.0~\text{V} < \text{V}_{\text{BAT}} < 4.5~\text{V},~\text{I}_{\text{LOAD}}$ from 0 to $500~\text{mA}$	4.77	5.07	5.17	V
I _{BAT(BOOST)}	Boost Mode Quiescent Current	PFM Mode, V _{BAT} =3.6 V, I _{OUT} =0		140	300	μА
I _{LIMPK(BST)}	Q2 Peak Current Limit		1440	1700	1960	mA
	Minimum Battery Voltage for	While Boost Active		2.30		.,
UVLO _{BST}	Boost Operation	To Start Boost Regulator		2.50	2.70	- V

Electrical Specifications

Unless otherwise specified: according to the circuit of Figure 1; recommended operating temperature range for T_J and T_A ; $V_{BUS}=5.0 \text{ V}$; HZ_MODE ; $QPA_MODE=0$; $QPA_MODE=$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
VBUS Loa	id Resistance					· I
D	VPLIC to DOND Desistance	Normal Operation		1500		kΩ
R_{VBUS}	VBUS to PGND Resistance	Charger Validation		100		Ω
Protection	and Timers					•
\/D!!6	VBUS Over-Voltage Shutdown	V _{BUS} Rising	6.09	6.29	6.49	V
VBUS _{OVP}	Hysteresis	V _{BUS} Falling		100		mV
I _{LIMPK(CHG)}	Q1 Cycle-by-Cycle Peak Current Limit	Charge Mode		2.3		Α
V	Battery Short-Circuit Threshold	V _{BAT} Rising	1.95	2.00	2.05	V
V_{SHORT}	Hysteresis	V _{BAT} Falling	24	100	0	mV
I _{SHORT}	Linear Charging Current	V _{BAT} < V _{SHORT}	20	30	40	mA
- /	Thermal Shutdown Threshold ⁽⁶⁾	T _J Rising	Y	145		- °C
T _{SHUTDWN}	Hysteresis ⁽⁶⁾	T _J Falling		10		
T_{CF}	Thermal Regulation Threshold ⁽⁶⁾	Charge Current Reduction Begins		120		°C
t _{INT}	Detection Interval		A	2.1		S
	32-Second Timer ⁽⁷⁾	Charger Enabled	20.5	25.2	28.0	
t _{32S}	32-Second Timer	Charger Disabled	18.0	25.2	34.0	S
t _{15MIN}	15-Minute Timer	15-Minute Mode	12.0	13.5	15.0	min
Δt_{LF}	Low-Frequency Timer Accuracy	Charger Inactive	-25		25	%

Notes

- 4. Negative current is current flowing from the battery to GND (discharging the battery).
- 5. Q2 always turns on for 60 ns, then turns off if current is below I_{SYNC}.
- 6. Guaranteed by design; not tested in production.
- 7. This tolerance (%) applies to all timers on the IC, including soft-start and deglitching timers.

I²C Timing Specifications

Guaranteed by design, $V_{BAT} \ge 2.5 \text{ V}$ if valid VBUS not present.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Uni
		Standard Mode			100	
	SCL Clock Frequency	Fast Mode			400	1.11
f _{SCL}		High-Speed Mode, C _B ≤ 100 pF			3400	kH
		High-Speed Mode, C _B ≤ 400 pF			1700	
	Bus-Free Time between STOP	Standard Mode		4.7		
t _{BUF}	and START Conditions	Fast Mode		1.3		μ
	e=3	Standard Mode		4		μ
t _{HD;STA}	START or Repeated START Hold Time	Fast Mode		600		ns
	Tiola Time	High-Speed Mode	/	160		ns
	/	Standard Mode		4.7		μ
		Fast Mode		1.3		μ
t _{LOW}	SCL LOW Period	High-Speed Mode, C _B ≤ 100 pF	1	160		n:
	Y.	High-Speed Mode, C _B ≤ 400 pF	70	320		n
		Standard Mode		4		μ
	SCL HIGH Period	Fast Mode		600		n
t _{HIGH}		High-Speed Mode, C _B ≤ 100 pF		60		n
		High-Speed Mode, C _B ≤ 400 pF		120		n
		Standard Mode		4.7		μ
t _{SU;STA}	Repeated START Setup Time	Fast Mode		600		n
		High-Speed Mode		160		n
	Data Setup Time	Standard Mode		250		
t _{SU:DAT}		Fast Mode		100		n
,		High-Speed Mode		10		
ll l		Standard Mode	0		3.45	μ
		Fast Mode	0		900	n
t _{HD;DAT}	Data Hold Time	High-Speed Mode, C _B ≤ 100 pF	0		70	n
		High-Speed Mode, C _B ≤ 400 pF	0		150	n
		Standard Mode	20+0).1C _B	1000	
		Fast Mode		0.1C _B	300	1
t _{RCL}	SCL Rise Time	High-Speed Mode, C _B ≤ 100 pF		10	80	n
		High-Speed Mode, C _B ≤ 400 pF		20	160	1
		Standard Mode	20+0).1C _B	300	
		Fast Mode	20+0	0.1C _B	300	
t _{FCL}	SCL Fall Time	High-Speed Mode, C _B ≤ 100 pF		10	40	n
		High-Speed Mode, C _B ≤ 400 pF		20	80	
	CDA Dies Tirre	Standard Mode	20+0).1C _B	1000	
t _{RDA}	SDA Rise Time Rise Time of SCL after a	Fast Mode	20+0).1C _B	300	1
t _{RCL1}	Repeated START Condition	High-Speed Mode, C _B ≤ 100 pF		10	80	n
	and after ACK Bit	High-Speed Mode, C _B ≤ 400 pF		20	160	1

Continued on the following page...

I²C Timing Specifications

Guaranteed by design, V_{BAT}≥2.5 V if valid VBUS not present.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
	SDA Fall Time	Standard Mode	20+0).1C _B	300		
		Fast Mode	20+0).1C _B	300		
t _{FDA}		High-Speed Mode, C _B ≤ 100 pF		10	80	ns	
		High-Speed Mode, C _B ≤ 400 pF		20	160		
	Stop Condition Setup Time	Standard Mode		4		μS	
t _{SU;STO}		Fast Mode		600		ns	
		High-Speed Mode		160		ns	
Св	Capacitive Load for SDA, SCL				400	pF	

Timing Diagrams

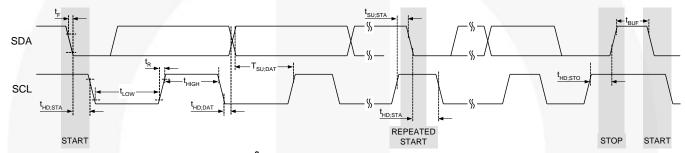
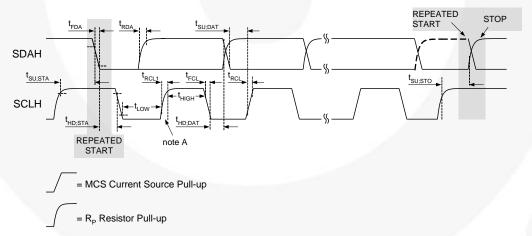


Figure 4. I²C Interface Timing for Fast and Slow Modes

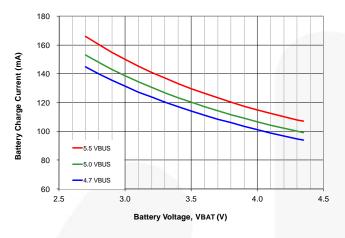


Note A: First rising edge of SCLH after Repeated Start and after each ACK bit.

Figure 5. I²C Interface Timing for High-Speed Mode

Charge Mode Typical Characteristics

Unless otherwise specified, circuit of Figure 1, V_{OREG}=4.2 V, V_{BUS}=5.0 V, and T_A=25°C.



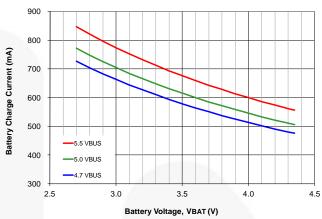


Figure 6. Battery Charge Current vs. V_{BUS} with I_{INLIM} =100 mA, V_{OREG} =4.35V

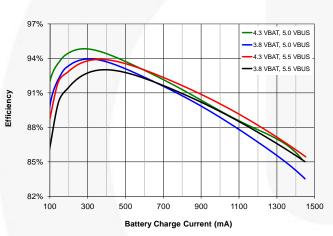


Figure 7. Battery Charge Current vs. V_{BUS} with I_{INLIM} =500 mA, V_{OREG} =4.35V

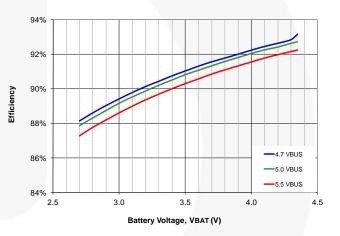


Figure 8. Charger Efficiency, No I_{INLIM}, I_{OCHARGE}=1450 mA

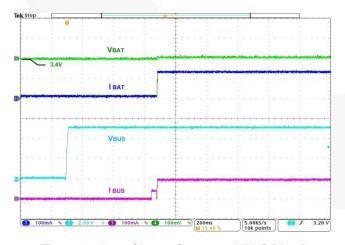


Figure 9. Charger Efficiency vs. V_{BUS} , I_{INLIM} =500 mA, V_{OREG} =4.35

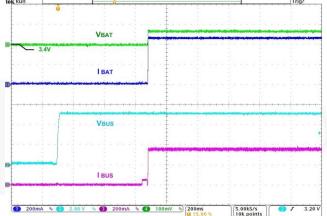


Figure 10. Auto-Charge Startup at VBUS Plug-in, OTG=0, V_{BAT} =3.4 V

Figure 11. Auto-Charge Startup at VBUS Plug-in, OTG=1, V_{BAT}=3.4 V

Charge Mode Typical Characteristics Unless otherwise specified, circuit of Figure 1, V_{OREG}=4.2 V, V_{BUS}=5.0 V, and T_A=25°C. VBAT IBUS Figure 12. Auto-Charge Startup with 300 mA Limited Figure 13. Charger Startup with HZ_MODE Bit Reset, Charger / Adaptor, OTG=1, V_{BAT}=3.4 V I_{INLIM}=500 mA, I_{OCHARGE}=1050 mA, V_{OREG}=4.2 V, V_{BAT}=3.6 V Figure 14. Battery Removal / Insertion During Charging, Figure 15. Battery Removal / Insertion During Charging, V_{BAT}=3.9 V, I_{OCHARGE}=1050 mA, No I_{INLIM}, TE=0 V_{BAT}=3.9 V, I_{OCHARGE}=1050 mA, No I_{INLIM}, TE=1 1.82 250 - -30C 200 High-Z Mode Input Current (μA) 150 VREG (V) 100 1.79

Figure 16. **VBUS Current in High-Impedance Mode** with Battery Open

Input Voltage, VBUS (V)

5.0

Figure 17. V_{REG} 1.8 V Output Regulation

1.8V Regulator Load Current (mA)

-30C, 5.0 VBUS

+25C, 5.0 VBUS +85C, 5.0 VBUS

1 78

1.77

4.5

50

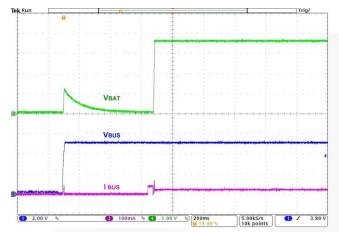
0

4.0

6.0

Charge Mode Typical Characteristics

Unless otherwise specified, circuit of Figure 1, V_{OREG}=4.2 V, V_{BUS}=5.0 V, and T_A=25°C.



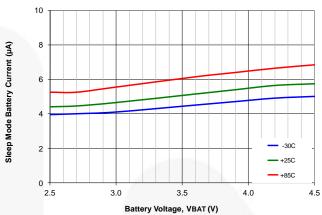


Figure 18. No Battery, TE=0, V_{BUS} Power Up

Figure 19. Sleep Mode Battery Discharge Current, SDA=SCL=0 V, VBUS open

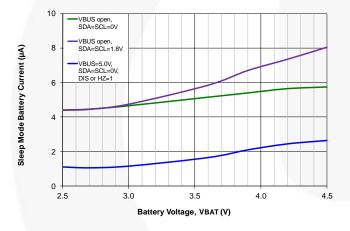
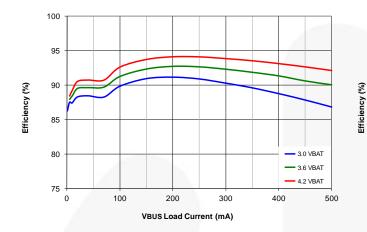


Figure 20. Battery Discharge Current vs. Mode

Boost Mode Typical Characteristics

Unless otherwise specified, using circuit of Figure 1 V_{BAT}=3.6 V, T_A=25°C.



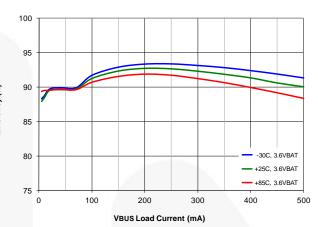
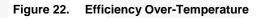
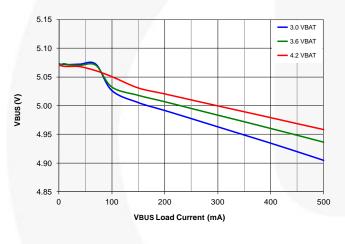


Figure 21. Efficiency vs. V_{BAT}





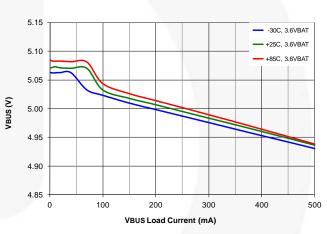


Figure 23. Output Regulation vs. VBAT

Figure 24. Output Regulation Over-Temperature

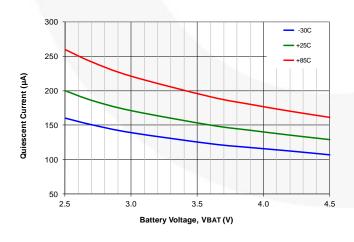
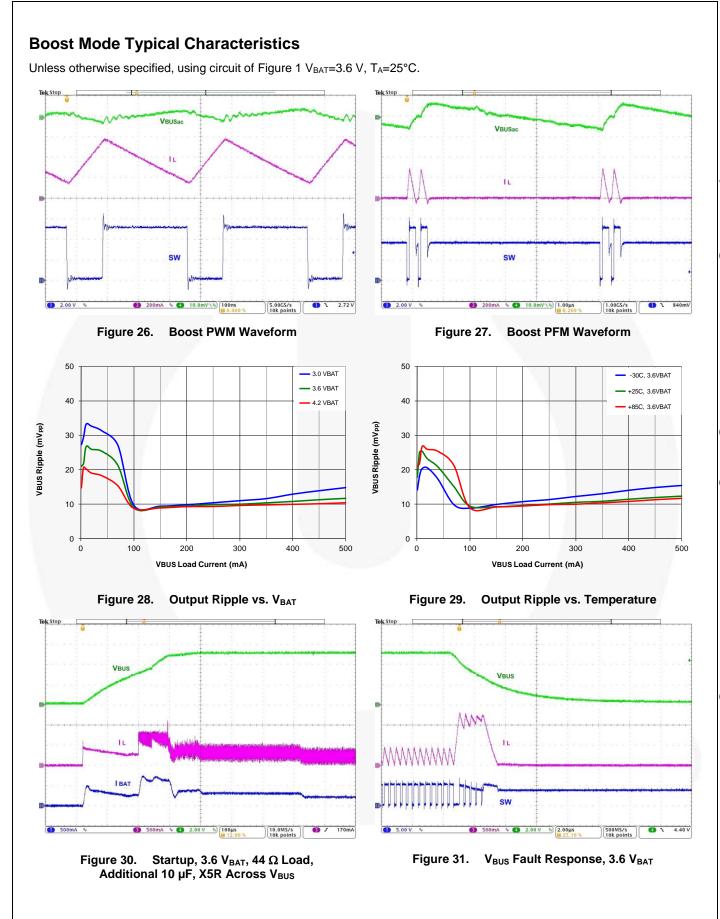
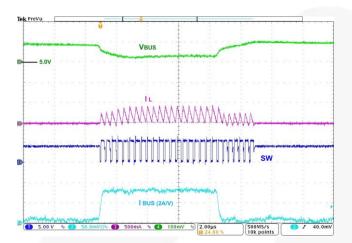


Figure 25. Quiescent Current



Boost Mode Typical Characteristics

Unless otherwise specified, using circuit of Figure 1 V_{BAT} =3.6 V, T_A =25°C.



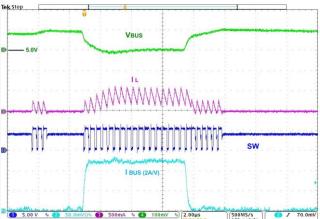


Figure 32. Load Transient, 5-155-5 mA, t_R=t_F=100 ns

Figure 33. Load Transient, 5-255-5 mA, t_R=t_F=100 ns

Circuit Description / Overview

When charging batteries with a current-limited input source, such as USB, a switching charger's high efficiency over a wide range of output voltages minimizes charging time.

The FAN54005 combines a highly integrated synchronous buck regulator for charging with a synchronous boost regulator, which can supply 5 V to USB On-The-Go (OTG) peripherals. The FAN54005 employs synchronous rectification for both the charger and boost regulators to maintain high efficiency over a wide range of battery voltages and charge states.

The FAN54005 has three operating modes:

- Charge Mode: Charges a single-cell Li-ion or Li-polymer battery.
- Boost Mode: Provides 5 V power to USB-OTG with an integrated synchronous rectification boost regulator using the battery as input.
- High-Impedance Mode:
 Both the boost and charging circuits are OFF in this mode. Current flow from VBUS to the battery or from the battery to VBUS is blocked in this mode. This mode consumes very little current from VBUS or the battery.

Charge Mode and Registers

Note: Default settings are denoted by **bold typeface**.

Charge Mode

In Charge Mode, FAN54005 employs four regulation loops:

- Input Current: Limits the amount of current drawn from VBUS. This current is sensed internally and can be programmed through the I²C interface.
- Charging Current: Limits the maximum charging current. This current is sensed using an external R_{SENSE} resistor.
- 3. Charge Voltage: The regulator is restricted from exceeding this voltage. As the internal battery voltage rises, the battery's internal impedance and R_{SENSE} work in conjunction with the charge voltage regulation to decrease the amount of current flowing to the battery. Battery charging is completed when the voltage across R_{SENSE} drops below the threshold determined by I_{TERM}.
- Temperature: If the IC's junction temperature reaches 120°C, charge current is reduced until the IC's temperature stabilizes at 120°C.
- Dynamic Input Voltage Control (DIVC) limits the amount of drop on VBUS to a programmable voltage (V_{SP}) to accommodate incompatible adapters that limit current to a lower current than might be available from a "normal" USB adapter.

Battery Charging Curve

If the battery voltage is below V_{SHORT} , a linear current source pre-charges the battery until V_{BAT} reaches V_{SHORT} . The PWM charging circuit is then started and the battery is charged

with a constant current if sufficient input power is available. The current slew rate is limited to prevent overshoot.

During the current regulation phase of charging, I_{INLIM} or the programmed charging current limits the amount of current available to charge the battery and power the system. The effect of I_{INLIM} on I_{OCHARGE} can be seen in Figure 35.

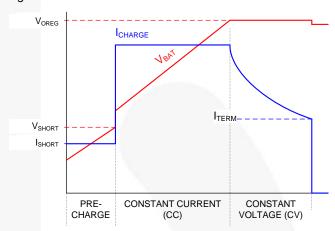


Figure 34. Charge Curve, I_{OCHARGE} Not Limited by I_{INLIM}

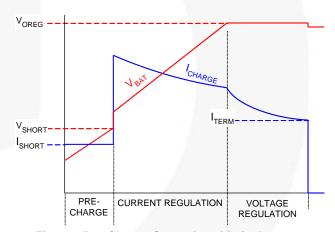


Figure 35. Charge Curve, I_{INLIM} Limits I_{OCHARGE}

Assuming that V_{OREG} is programmed to the cell's fully charged "float" voltage, the current that the battery accepts with the PWM regulator limiting its output (sensed at VBAT) to V_{OREG} declines, and the charger enters the voltage regulation phase of charging. When the current declines to the programmed I_{TERM} value, the charge cycle is complete. Charge current termination can be disabled by resetting the TE bit (REG 01[3]).

The charger output or "float" voltage can be programmed by the OREG bits from 3.5 V to 4.44 V in 20 mV increments as shown in Table 2.

Table 2. OREG Bits (REG 02[7:2]) vs. Charger $V_{\text{OUT}}\left(V_{\text{OREG}}\right)$ Float Voltage

ORE		
Decimal	Hex	V _{OREG}
0	00	3.50
1	01	3.52
2	02	3.54
3	03	3.56
4	04	3.58
5	05	3.60
6	06	3.62
7	07	3.64
8	08	3.66
9	09	3.68
10	0A	3.70
11	0B	3.72
12	0C	3.74
13	0D	3.76
14	0E	3.78
15	0F	3.80
16	10	3.82
17	11	3.84
18	12	3.86
19	13	3.88
20	14	3.90
21	15	3.92
22	16	3.94
23	17	3.96
24	18	3.98
25	19	4.00
26	1A	4.02
27	1B	4.04
28	1C	4.06
29	1D	4.08
30	1E	4.10

Decimal	Hex	V_{OREG}
32	20	4.14
33	21	4.16
34	22	4.18
35	23	4.20
36	24	4.22
37	25	4.24
38	26	4.26
39	27	4.28
40	28	4.30
41	29	4.32
42	2A	4.34
43	2B	4.36
44	2C	4.38
45	2D	4.40
46	2E	4.42
47	2F	4.44
48	30	4.44
49	31	4.44
50	32	4.44
51	33	4.44
52	34	4.44
53	35	4.44
54	36	4.44
55	37	4.44
56	38	4.44
57	39	4.44
58	ЗА	4.44
59	3B	4.44
60	3C	4.44
61	3D	4.44
62	3E	4.44

The following charging parameters can be programmed by the host through I^2C :

Table 3. Programmable Charging Parameters

Parameter	Name	Register
Output Voltage Regulation	Voreg	REG 02[7:2]
Battery Charging Current Limit	I _{OCHARGE}	REG 04[6:4]
Input Current Limit	I _{INLIM}	REG 01[7:6]
Charge Termination Limit	I _{TERM}	REG 04[2:0]
Weak Battery Voltage	V_{LOWV}	REG 01[5:4]

A new charge cycle begins when one of the following occurs:

- The battery voltage falls below V_{OREG} V_{RCH}
- VBUS Power on Reset (POR)
- CE or HZ_MODE is reset through I²C write to CONTROL1 (REG 01) register.

Charge Current Limit (I_{OCHARGE})

Charge current is limited by the IO_LEVEL (Reg 05[5]) bit by default (IO_LEVEL=1). This limits charge current to 500 mA when $R_{\text{SENSE}}{=}68~\text{m}\Omega$ and 340 mA when $R_{\text{SENSE}}{=}100~\text{m}\Omega$. When IO_LEVEL=0 charge current is limited by the IOCHARGE bits.

Table 4. $I_{OCHARGE}$ Current as Function of IOCHARGE (REG 04 [6:4]) Bits and R_{SENSE} Resistor Values

IOCHA	RGE			
Decimal	HEX	V _{RSENSE} I _{OCHARO}		_{GE} (mA)
Decimal	ПЕХ	(mV)	68 mΩ	100 mΩ
0	00	37.4	550	374
1	01	44.2	650	442
2	02	51.0	750	510
3	03	57.8	850	578
4	04	71.4	1050	714
5	05	78.2	1150	782
6	06	91.8	1350	918
7	07	98.6	1450	986

Termination Current Limit

Current charge termination is enabled when TE (REG 01[3])=1.

Table 5. I_{TERM} Current as Function of ITERM Bits (REG 04[2:0]) and R_{SENSE} Resistor Values

ITE	RM			
Decimal	HEX	V _{RSENSE}	I _{TERM} (mA)	
Decimal	ПЕХ	(mV)	68 mΩ	100 mΩ
0	00	3.3	49	33
1	01	6.6	97	66
2	02	9.9	146	99
3	03	13.2	194	132
4	04	16.5	243	165
5	05	19.8	291	198
6	06	23.1	340	231
7	07	26.4	388	264

When the charge current falls below I_{TERM}, PWM charging stops and the STAT bits change to READY (00) for about 500 ms while the IC determines whether the battery and charging source are still connected. STAT then changes to CHARGE DONE (10), provided the battery and charger are still connected.

PWM Controller in Charge Mode

The IC uses a current-mode PWM controller to regulate the output voltage and battery charge currents. The synchronous rectifier (Q2) has a current limit that which off the FET when the current is negative by more than 140 mA peak. This prevents current flow from the battery.

Charger Operation

V_{BUS} Plug In

When the IC detects that V_{BUS} has risen above $V_{IN(MIN)1}$ (4.4 V), the IC applies a 100 Ω load from VBUS to GND. To clear the VBUS Power-On-Reset (POR) and begin charging, VBUS must remain above $V_{IN(MIN)1}$ and below VBUS_{OVP} for t_{VBUS_VALID} (30 ms) before the IC initiates charging.

The VBUS validation sequence always occurs before charging is initiated or re-initiated (for example, after a VBUS OVP fault or a $V_{\rm RCH}$ recharge initiation).

 T_{VBUS_VALID} ensures that unfiltered 50 / 60 Hz chargers and other non-compliant chargers are rejected.

Safety Timer

Section references Figure 39.

At the beginning of charging, the IC starts a 15-minute timer ($t_{15\text{MIN}}$). When this times out, charging is terminated. Writing to any register through I²C stops and resets the $t_{15\text{MIN}}$ timer, which in turn starts a 32-second timer ($t_{32\text{S}}$). Setting the TMR_RST bit (REG 00[7]) resets the $t_{32\text{S}}$ timer. If the $t_{32\text{S}}$ timer times out; charging is terminated, all registers (except Safety) are set to their default values, the FAULT bits are set to 110, STAT is pulsed HIGH and returns LOW, and charging resumes using the default values with the $t_{15\text{MIN}}$ timer running.

Normal charging is controlled by the host with the t_{328} timer running to ensure that the host is alive. Charging with the $t_{15\text{MIN}}$ timer running is used for charging that is unattended by the host. If the $t_{15\text{MIN}}$ timer expires; the IC turns off the charger, sets the $\overline{\text{CE}}$ bit, and indicates a timer fault (110) on the FAULT bits (REG 00[2:0]). This sequence prevents overcharge if the host fails to reset the t_{328} timer.

USB-Friendly Boot Sequence

At VBUS POR, the IC operates in accordance with its I²C register settings. If no registers have been written (including Safety, and the TMR_RST bit), typically due to an absence of host communication, the chargers input current limit is controlled by the OTG pin (100 mA if OTG is LOW and 500 mA if OTG is HIGH).

Once the host processor begins writing to the IC, charging parameters are set by the host, which must continually reset the t_{32S} timer to continue charging using the programmed charging parameters.

Input Current Limiting

To minimize charging time without overloading VBUS current limitations, the IC's input current limit can be programmed by the IINLIM bits (REG 01[7:6]).

Table 6. Input Current Limit

IINLIM REG 01[7:6]	Input Current Limit
00	100 mA
01	500 mA
10	800 mA
11	No limit

The OTG pin establishes the input current limit when $t_{15\text{MIN}}$ is running.

Flow Charts

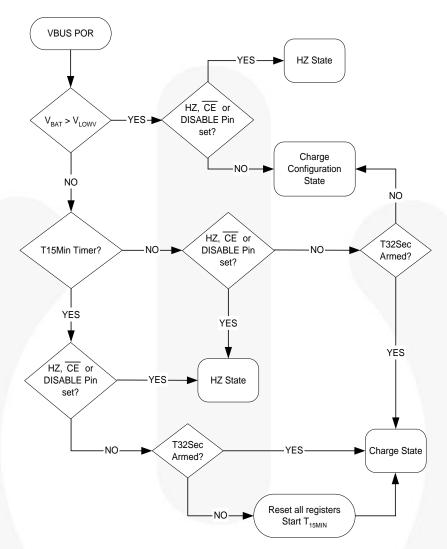


Figure 36. Charger VBUS POR

Flow Charts (Continued) CHARGE STATE Disable Charging Indicate **VBUS** Fault Enable I_{SHORT}, Reset Safety reg VBUS OK? $V_{BAT} < V_{SHORT}$ NO Indicate Charging NO YES PWM Charging VBUS OK? T_{15MIN} Indicate Charging Timeout? NO YES Disable Charging Indicate timer fault Charge $\mathsf{T}_{\mathsf{15MIN}}$ Configuration Timeout? Set CE Indicate State **VBUS** Fault NO HIGHZ mode $I_{\rm OUT} < I_{\rm TERM}$ Indicate Charge $V_{BAT} < V_{OREG} - V_{RCH}$ YES Termination enabled NO Complete $V_{BAT} > V_{OREG} - V_{RCH}$ Reset Safety reg NO Delay $t_{\rm INT}$ YES Battery Removed Stop Charging $V_{BAT} < V_{OREG} - V_{RCH}$ Reset charge Enable IDET for T_{DETECT} parameters Figure 37. **Charge Mode**

Flow Charts (Continued)

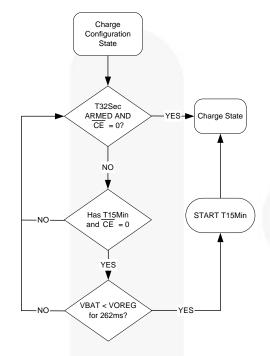


Figure 38. Charge Configuration

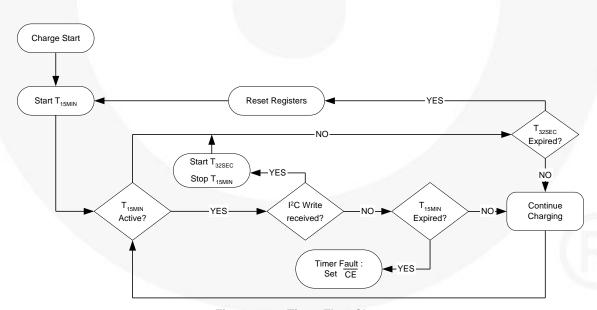


Figure 39. Timer Flow Chart

Dynamic Input Voltage Control

The FAN54005 has functionality that limits input current in case a current-limited incompatible adapter is supplying VBUS. These slowly increase the charging current until either:

I_{INLIM} or I_{OCHARGE} is reached

or

V_{BUS}=V_{SP}.

If V_{BUS} collapses to V_{SP} when the current is ramping up, the FAN54005 charges with an input current that keeps V_{BUS} = V_{SP} . When the V_{SP} control loop is limiting the charge current, the SP bit (REG 05[4]) is set.

Table 7. V_{SP} as Function of VSP Bits (REG 05[2:0])

V		
Decimal	HEX	V _{SP}
0	00	4.213
1	01	4.293
2	02	4.373
3	03	4.453
4	04	4.533
5	05	4.613
6	06	4.693
7	07	4.773

Safety Settings

FAN54005 contain a SAFETY register (REG 06) that prevents the values in OREG (REG 02[7:2]) and IOCHARGE (REG 04[6:4]) from exceeding the values of the VSAFE and ISAFE values. *Refer to Table 8 and Table 9 for details*.

After V_{BAT} exceeds V_{SHORT} , the SAFETY register is loaded with its default value and may be written only before any other register is written. The entire desired Safety register value should be written twice to ensure the register bits are set. After writing to any other register, the SAFETY register is locked until V_{BAT} falls below V_{SHORT} .

The ISAFE (REG 06[6:4]) and VSAFE (REG 06[3:0]) registers establish values that limit the maximum values of $I_{\rm OCHARGE}$ and $V_{\rm OREG}$ used by the control logic. If the host attempts to write a value higher than VSAFE or ISAFE to OREG or IOCHARGE, respectively; the VSAFE, ISAFE value appears as the OREG, IOCHARGE register value, respectively.

Table 8. I_{SAFE} (I_{OCHARGE} Limit) as Function of ISAFE Bits (REG 06[6:4])

ISA	FE			
Decimal	шту	V _{RSENSE}	I _{SAFE}	(mA)
Decimal	HEX	(mV)	68 mΩ	100 mΩ
0	00	37.4	550	374
1	01	44.2	650	442
2	02	51.0	750	510
3	03	57.8	850	578
4	04	71.4	1050	714
5	05	78.2	1150	782
6	06	91.8	1350	918
7	07	98.6	1450	986

Table 9. V_{SAFE} (V_{OREG} Max. Limit) as Function of VSAFE Bits (REG 06[3:0])

VSA	FE		
Decimal	HEX	Max. OREG (REG V _{OREG} 02[7:2]) Max. (
0	00	100011	4.20
1	01	100100	4.22
2	02	100101	4.24
3	03	100110	4.26
4	04	100111	4.28
5	05	101000	4.30
6	06	101001	4.32
7	07	101010	4.34
8	08	101011	4.36
9	09	101100	4.38
10	0A	101101	4.40
11	0B	101110	4.42
12	0C	101111	4.44
13	0D	110000	4.44
14	0E	110001	4.44
15	0F	110010	4.44

Thermal Regulation and Protection

When the IC's junction temperature reaches T_{CF} (about 120°C), the charger reduces its output current to 550 mA to prevent overheating. If the temperature increases beyond $T_{SHUTDOWN}$; charging is suspended, the FAULT bits are set to 101, and STAT is pulsed HIGH. In Suspend Mode, all timers stop and the state of the IC's logic is preserved. Charging resumes at programmed current after the die cools to about 120°C.

Additional θ_{JA} data points, measured using the FAN54005 evaluation board, are given in Table 10 (measured with $T_A\!=\!25^{\circ}\!C).$ Note that as power dissipation increases, the effective θ_{JA} decreases due to the larger difference between the die temperature and ambient.

Table 10. Evaluation Board Measured θ_{JA}

Power (W)	θ_{JA}
0.504	54°C/W
0.844	50°C/W
1.506	46°C/W

Charge Mode Input Supply Protection Sleep Mode

When V_{BUS} falls below V_{BAT} + V_{SLP} , and V_{BUS} is above $V_{IN(MIN)1}$, the IC enters Sleep Mode to prevent the battery from draining into VBUS. During Sleep Mode, reverse current is disabled by body switching Q1.

Input Supply Low-Voltage Detection

The IC continuously monitors VBUS during charging. If V_{BUS} falls below $V_{IN(MIN)2}$, the IC:

- 1. Terminates charging
- Pulses the STAT pin, sets the STAT bits to 11, and sets the FAULT bits to 011.

If V_{BUS} recovers above the $V_{\text{IN(MIN)}1}$ rising threshold after time t_{INT} (about two seconds), the charging process is repeated. This function prevents the USB power bus from collapsing or oscillating when the IC is connected to a suspended USB port or a low-current-capable OTG device.

Input Over-Voltage Detection

When V_{BUS} exceeds VBUS_{OVP}, the IC:

- Turns off Q3
- 2. Suspends charging
- Sets the FAULT bits to 001, sets the STAT bits to 11, and pulses the STAT pin.

When V_{BUS} falls about 100 mV below VBUS_{OVP}, the fault is cleared and charging resumes after V_{BUS} is revalidated.

VBUS Short While Charging

If VBUS is shorted with a very low impedance while the IC is charging with I_{INLIMIT} =100 mA, the IC may not meet datasheet specifications until power is removed. To trigger this condition, V_{BUS} must be driven from 5 V to GND with a high slew rate. Achieving this slew rate requires a 0 Ω short from GND to the USB cable that is less than 10 cm from the connector.

Charge Mode Battery Detection & Protection VBAT Over-Voltage Protection

The OREG voltage regulation loop prevents V_{BAT} from overshooting the OREG voltage by more than 50 mV when the battery is removed. When the PWM charger runs with no battery, the TE bit is not set, and a battery is inserted that is charged to a voltage higher than V_{OREG} ; PWM pulses stop. If no further pulses occur for 30 ms, the IC sets the FAULT bits to 100, sets the STAT bits to 11, and pulses the STAT pin.

Battery Detection during Charging

The IC can detect the presence, absence, or removal of a battery if the termination bit (TE) is set. During normal charging, once V_{BAT} is close to V_{OREG} and the termination charge current is detected, the IC terminates charging and sets the STAT bits to 10. It then turns on a discharge current, I_{DETECT} , for I_{DETECT} . If V_{BAT} is still above $V_{\text{OREG}}-V_{\text{RCH}}$, the battery is present and the IC sets the FAULT bits to 000. If V_{BAT} is below $V_{\text{OREG}}-V_{\text{RCH}}$, the battery is absent and the IC:

- 1. Sets the registers to their default values.
- 2. Sets the FAULT bits to 111.
- Resumes charging with default values after t_{INT}.

Battery Short-Circuit Protection

If the battery voltage is below the short-circuit threshold (V_{SHORT}); a linear current source, I_{SHORT} , supplies V_{BAT} until $V_{BAT} > V_{SHORT}$.

System Operation with No Battery

The FAN54005 continues charging after VBUS POR with the default parameters, regulating the V_{BAT} line to 3.54 V until the host processor issues commands or the $t_{15\text{MIN}}$ timer expires. In this way, the FAN54005 can start the system without a battery.

The FAN54005 soft-start function can interfere with the system supply with battery absent. The soft-start activates whenever $V_{\rm OREG}$, $I_{\rm INLIM}$, or $I_{\rm OCHARGE}$ are set from a lower to higher value. During soft-start, the $I_{\rm IN}$ limit drops to 100 mA for about 1 ms unless IINLIM is set to 11 (no limit). This could cause the system processor to fail to start. To avoid this behavior, use the following sequence.

- Set the OTG pin HIGH. When VBUS is plugged in, I_{INLIM} is set to 500 mA until the system processor powers up and can set parameters through I²C.
- 2. Program the Safety Register.
- Set IINLIM to 11 (no limit).
- 4. Set OREG to the desired value (typically 4.18).
- Reset the IO_LEVEL bit, then set IOCHARGE.
- 6. Set I_{INLIM} to 500 mA if a USB source is connected.

During the initial system startup, while the charger IC is being programmed, the system current is limited to 500 mA for 1 ms during steps 4 and 5. This is the value of the soft-start $I_{\rm OCHARGE}$ current used when $I_{\rm INLIM}$ is set to No Limit.

If the system is powered up without a battery present, the CV bit should be set. When a battery is inserted, the CV bit is cleared.

Charger Status / Fault Status

The STAT pin indicates the operating condition of the IC and provides a fault indicator for interrupt driven systems.

Table 11. STAT Pin Function

EN_STAT	Charge State	STAT Pin
0	X	OPEN
Х	Normal Conditions	OPEN
1	Charging	LOW
Х	Fault (Charging or Boost)	128 μs Pulse, then OPEN

The FAULT bits (REG 00[2:0]) indicate the type of fault in Charge Mode. See Table 12 for details.

Table 12. Fault Status Bits During Charge Mode

F	Fault Bit		Foult Description		
B2	B1	В0	Fault Description		
0	0	0	Normal (No Fault)		
0	0	1	VBUS OVP		
0	1	0	Sleep Mode		
0	1	1	Poor Input Source		
1	0	0	Battery OVP		
1	0	1	Thermal Shutdown		
1	1	0	Timer Fault		
1	1	1	No Battery		

Charge Mode Control Bits

Setting either HZ_MODE or CE through I²C disables the charger and puts the IC into High-Impedance Mode. The t_{32S} timer will continue to run. If it is allowed to expire, all registers (except SAFETY) reset, which enables $\underline{t_{15MIN}}$ charging. When the t_{15MIN} expires, the IC sets the $\overline{\text{CE}}$ bit and the IC enters High-Impedance Mode. If $\overline{\text{CE}}$ was set by t_{15MIN} overflow, a new charge cycle can only be initiated through I²C or VBUS POR.

Setting the RESET bit clears all registers (except Safety).

Table 13. DISABLE Pin and CE Bit Functionality

Charging	DISABLE Pin	CE	HZ_MODE
ENABLE	0	0	0
DISABLE	X	1	X
DISABLE	X	Х	1
DISABLE	1	Х	Х

Raising the DISABLE pin does stop the t_{32S} from advancing. If the DISABLE pin is raised during $t_{15\text{MIN}}$ charging, the $t_{15\text{MIN}}$ timer is reset.

Operational Mode Control

OPA_MODE (REG 01[0]) and the HZ_MODE (REG 01[1]) bits in conjunction with the FAULT state define the operational mode of the charger.

Table 14. Operation Mode Control

HZ_MODE	OPA_MODE	FAULT	Operation Mode
0	0	0	Charge
0	X	1	Charge Configure
0	1	0	Boost
1	X	Х	High Impedance

The IC resets the OPA_MODE bit whenever the boost is deactivated, whether due to a fault or being disabled by setting the HZ_MODE bit.

Boost Mode

Boost Mode can be enabled if the IC is in 32-Second Mode with the OTG pin and OPA_MODE bits as indicated in Table 15. The OTG pin ACTIVE state is 1 if OTG_PL=1 and 0 when OTG_PL=0.

If boost is active using the OTG pin, Boost Mode is initiated even if the HZ_MODE=1. The HZ_MODE bit overrides the OPA_MODE bit.

Table 15. Enabling Boost

OTG_EN	OTG Pin	HZ_ MODE	OPA_ MODE	BOOST
1	ACTIVE	Х	X	Enabled
Х	X	0	1	Enabled
X	ACTIVE	Х	0	Disabled
0	Х	1	Х	Disabled
1	ACTIVE	1	1	Disabled
0	ACTIVE	0	0	Disabled

To remain in Boost Mode, the TMR_RST must be set by the host before the t_{32S} timer times out. If t_{32S} times out in Boost Mode; the IC resets all registers, pulses the STAT pin, sets the FAULT bits to 110, and resets the BOOST bit. VBUS POR or reading REG00 clears the fault condition.

Boost PWM Control

The IC uses a minimum on-time and computed minimum off-time to regulate VBUS. The regulator achieves excellent transient response by employing current-mode modulation. This technique causes the regulator to exhibit a load line. During PWM Mode, the output voltage drops slightly as the input current rises. With a constant V_{BAT} , this appears as a constant output resistance.

The "droop" caused by the output resistance when a load is applied allows the regulator to respond smoothly to load transients with no undershoot from the load line. *This can be seen in Figure 32 and Figure 40.*

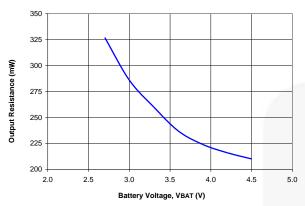


Figure 40. Output Resistance (R_{OUT})

 V_{BUS} as a function of I_{LOAD} can be computed when the regulator is in PWM Mode (continuous conduction) as:

$$V_{BUS} = 5.07 - R_{OUT} \bullet I_{LOAD} \tag{1}$$

At V_{BAT}=3.3 V, and I_{LOAD}=200 mA, V_{BUS} would drop to:

$$V_{BUS} = 5.07 - 0.26 \bullet 0.2 = 5.018V \tag{1A}$$

At V_{BAT} =2.7 V, and I_{LOAD} =200 mA, V_{BUS} would drop to:

$$V_{RUS} = 5.07 - 0.327 \bullet 0.2 = 5.005V \tag{1B}$$

PFM Mode

If $V_{BUS} > V_{BOOST}$ (nominally 5.07 V) when the minimum off-time has ended, the regulator enters PFM Mode. Boost pulses are inhibited until $V_{BUS} < V_{BOOST}$. The minimum on-time is increased to enable the output to pump up sufficiently with each PFM boost pulse. Therefore the regulator behaves like a constant on-time regulator, with the bottom of its output voltage ripple at 5.07 V in PFM Mode.

Table 16. Boost PWM Operating States

Mode	Description	Invoked When
LIN	Linear Startup	V _{BAT} > V _{BUS}
SS	Boost Soft-Start	$V_{BUS} < V_{BOOST}$
BST	Boost Operating Mode	V _{BAT} > UVLO _{BST} and SS Completed

Startup

When the boost regulator is shut down, current flow is prevented from VBAT to VBUS, as well as reverse flow from VBUS to VBAT.

LIN State

When the boost is enabled, if $V_{BAT} > UVLO_{BST}$, the regulator first attempts to bring PMID within 400 mV of V_{BAT} using an internal 450 mA current source from VBAT (LIN State). If PMID has not achieved $V_{BAT} - 400$ mV after 560 μ s, a FAULT state is initiated.

SS State

When PMID > $V_{BAT}-400$ mV, the boost regulator begins switching with a reduced peak current limit of about 50% of its normal current limit. The output slews up until V_{BUS} is within 5% of its setpoint; at which time, the regulation loop is closed and the current limit is set to 100%.

If the output fails to achieve 95% of its setpoint (V_{BST}) within 128 μs , the current limit is increased to 100%. If the output fails to achieve 95% of its setpoint after this second 384 μs period, a fault state is initiated.

BST State

This is the normal operating mode of the regulator. The regulator uses a scheme of calculated t_{OFF} , modulated t_{ON} with a minimum t_{ON} . The calculated t_{OFF} is proportional to

 $\frac{V_{\text{IN}}}{V_{\text{OUT}}}$, which keeps the regulator's switching frequency

reasonably constant in CCM.

To ensure VBUS does not pump significantly above the regulation point, the boost switch remains off as long as the actual output voltage is greater than the regulation point.

Boost Faults

If a BOOST fault occurs:

- 1. The STAT pin pulses.
- 2. OPA MODE bit is reset.
- 3. The power stage is in High-Impedance Mode.
- 4. The FAULT bits (REG 00[2:0]) are set per Table 17

Restart After Boost Faults

If boost was enabled with the OPA_MODE bit and OTG_EN=0, Boost Mode can only be enabled through subsequent I²C commands since OPA_MODE is reset on boost faults. If OTG_EN=1 and the OTG pin is still ACTIVE (see Table 15), the boost restarts after a 5.2 ms delay, as shown in Figure 41. If the fault condition persists, restart is attempted every 5 ms until the fault clears or an I²C command disables the boost.

Table 17. Fault Bits During Boost Mode

Fa	ult I	Bit	Fault Description					
B2	В1	В0	Fault Description					
0	0	0	Normal (no fault)					
0	0	1	V _{BUS} > VBUS _{OVP}					
0	1	0	V_{BUS} fails to achieve the voltage required to advance to the next state during soft-start or sustained (>50 μ s) current limit during the BST state.					
0	1	1	V _{BAT} < UVLO _{BST}					
1	0	0	N/A: This code does not appear.					
1	0	1	Thermal shutdown					
1	1	0	Timer fault; all registers reset.					
1	1	1	N/A: This code does not appear.					

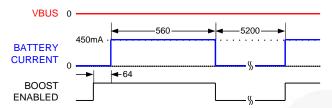


Figure 41. Boost Response Attempting to Start into VBUS Short Circuit (times in µs)

VREG Pin

The 1.8 V regulated output on this pin can be disabled through I^2C by setting the DIS_VREG bit (REG 05[6]). VREG can supply up to 2 mA. This circuit, which is powered from

PMID, is enabled only when PMID > V_{BAT} and does not drain current from the battery. During boost, V_{REG} is off. It is also off when the HZ_MODE bit (REG 01[1])=1.

Monitor Register (Reg 10h)

Additional status monitoring bits enable the host processor to have more visibility into the status of the IC. The monitor bits are real-time status indicators and are not internally debounced or otherwise time qualified.

The state of the MONITOR register bits listed in High-Impedance Mode is only valid when V_{BUS} is valid.

I²C Interface

The FAN54005's serial interface is compatible with Standard, Fast, Fast Plus, and High-Speed Mode I²C-Bus[®] specifications. The SCL line is an input and the SDA line is a bi-directional open-drain output; it can only pull down the bus when active. The SDA line only pulls LOW during data reads and signaling ACK. All data is shifted in MSB (bit 7) first.

Slave Address

Table 18. I²C Slave Address Byte

Part Type	7	6	5	4	3	2	1	0
FAN54005	1	1	0	1	0	1	0	R/W

In hex notation, the slave address assumes a 0 LSB. The hex slave address for the FAN54005 is D4H and is D6H for all other parts in the family.

Bus Timing

As shown in Figure 42, data is normally transferred when SCL is LOW. Data is clocked in on the rising edge of SCL. Typically, data transitions shortly at or after the falling edge of SCL to allow ample time for the data to set up before the next SCL rising edge.

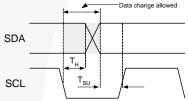


Figure 42. Data Transfer Timing

Each bus transaction begins and ends with SDA and SCL HIGH. A transaction begins with a START condition, which is defined as SDA transitioning from 1 to 0 with SCL HIGH, as shown in Figure 43.

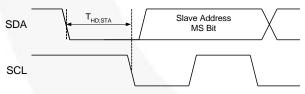


Figure 43. Start Bit

A transaction ends with a STOP condition, which is defined as SDA transitioning from 0 to 1 with SCL HIGH, as shown in Figure 44.

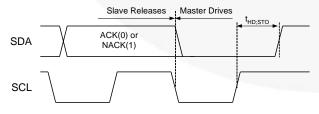


Figure 44. Stop Bit

During a read from the FAN54005 (Figure 47), the master issues a Repeated Start after sending the register address and before resending the slave address. The Repeated Start is a 1-to-0 transition on SDA while SCL is HIGH, as shown in Figure 45.

High-Speed (HS) Mode

The protocols for High-Speed (HS), Low-Speed (LS), and Fast-Speed (FS) Modes are identical except the bus speed for HS Mode is 3.4 MHz. HS Mode is entered when the bus master sends the HS master code 00001XXX after a start condition. The master code is sent in Fast or Fast Plus Mode (less than 1 MHz clock); slaves do not ACK this transmission.

The master then generates a repeated start condition (Figure 45) that causes all slaves on the bus to switch to HS Mode. The master then sends I²C packets, as described above, using the HS Mode clock rate and timing.

The bus remains in HS Mode until a stop bit (Figure 44) is sent by the master. While in HS Mode, packets are separated by repeated start conditions (Figure 45).

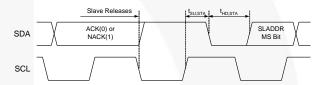


Figure 45. Repeated Start Timing

Read and Write Transactions

The figures below outline the sequences for data read and write. Bus control is signified by the shading of the packet,

defined as Master Drives Bus and All addresses and data are MSB first.

Table 19. Bit Definitions for Figure 46 and Figure 47

Symbol	Definition
S	START, see Figure 43
Α	ACK. The slave drives SDA to 0 to acknowledge the preceding packet.
Ā	NACK. The slave sends a 1 to NACK the preceding packet.
R	Repeated START, see Figure 45
Р	STOP, see Figure 44



Figure 46. Write Transaction



Figure 47. Read Transaction

Register Descriptions

The nine FAN54005 user-accessible registers are defined in Table 20.

Table 20. I²C Register Address

Register				Addre	ss Bits				
Name	REG#	7	6	5	4	3	2	1	0
CONTROL0	00	0	0	0	0	0	0	0	0
CONTROL1	01	0	0	0	0	0	0	0	1
OREG	02	0	0	0	0	0	0	1	0
IC_INFO	03	0	0	0	0	0	0	1	1
IBAT	04	0	0	0	0	0	1	0	0
SP_CHARGER	05	0	0	0	0	0	1	0	1
SAFETY	06	0	0	0	0	0	1	1	0
MONITOR	10h	0	0	0	0	1	0	1	0

Table 21. Register Bit Definitions

This table defines the operation of each register bit for all IC versions. Default values are in **bold** text.

Bit	Name	Value	Туре	Description				
CONT	ROL0			Register Address: 00 Default Value=X1XX 0XXX				
7	TMR_RST	4	W	Writing a 1 resets the t _{32S} timer; writing a 0 has no effect				
,	OTG	ı	R	Returns the OTG pin level (1=HIGH)				
6	EN STAT	0	R/W	Prevents STAT pin from going LOW during charging; STAT pin still pulses to enunciate faults				
		1		Enables STAT pin LOW when IC is charging				
		00	R	Ready				
E · 1	STAT	01		Charge in progress				
5.4	5:4 STAT 10			Charge done				
		11		Fault				
3	POOST	0	R	IC is not in Boost Mode				
3	BOOST	1		IC is in Boost Mode				
2:0	FAULT		R	Fault status bits: for Charge Mode, see Table 12				

Continued on the following page...

Register Bit Definitions (Continued)

Bit	Name	Value	Туре	Description				
CONT	ROL1			Register Address: 01	Default Value=0111 0000 (70h)			
7:6	IINLIM	01	R/W	Input current limit, see Table 6				
		00	R/W	3.4 V				
5.4	\/\ \O\\\\\	01		3.5 V	Wastalanda wastana dhasalada			
5:4	VLOWV	10		3.6 V	Weak battery voltage threshold			
		11		3.7 V				
		0	R/W	Disable charge current terminatio	n			
3	TE	1		Enable charge current termination				
_	_/	0	R/W	Charger enabled.				
2	CE	1		Charger disabled. The T _{32S} timer is r	not suspended			
	117 14005	0	R/W	Not High-Impedance Mode				
1	HZ_MODE	1		High-Impedance Mode	0 711 15			
		0	R/W	Charge Mode	See Table 15			
0	OPA_MODE	1		Boost Mode				
OREG		7	1	Register Address: 02	Default Value=0000 1010 (0Ah)			
7:2	OREG	000010	R/W	Charger output "float" voltage; prograincrements; defaults to 000010 (3.5	ammable from 3.5 to 4.44 V in 20 mV 54 V). See Table 2			
	0T0 PI	0	R/W	OTG pin active LOW				
1	OTG_PL	1		OTG pin active HIGH				
•	070 511	0	R/W	Disables OTG pin				
0	OTG_EN	1		Enables OTG pin				
IC_INF	- 0		I	Register Address: 03	Default Value=100101XX (9Xh)			
7:5	Vendor Code	100	R	Identifies Fairchild Semiconductor as	s the IC supplier			
4:2	PN	101	R	Part number bits, see the Ordering on page 2	Information			
1:0	REV	XX	R	IC Revision bits				
BAT				Register Address: 04	Default Value=1000 1001 (89h)			
7	RESET	1	W	Writing a 1 resets charge parameter defaults: writing a 0 has no effect; re	rs, except the Safety register (REG 06), to the ead returns 1			
6:4	IOCHARGE	000	R/W	Programs the maximum charge current when IO_LEVEL (REG 05[5]) = 0. See Table 4				
3	Reserved	1	R	Unused				
2:0	ITERM	001	R/W	Sets the current used for charging te	ermination. See Table 5			

Continued on the following page...

Register Bit Definitions (Continued)

SP_C	HARGER			Register Address: 05	Default Value=001X X100		
7	Reserved	0	R	Unused			
_	DIC VIDEO	0	R/W	1.8 V regulator is ON			
6	DIS_VREG	1		1.8 V regulator is OFF			
		0	R/W	Output current is controlled by	IOCHARGE bits		
5	IO_LEVEL	1		Output current control is set to and 340 mA for 100 m Ω)	34 mV across R _{SENSE} (500 mA for R _{SENSE} =68 m Ω		
4	SP	0	R	DIVC is not active (V _{BUS} is able	e to stay above V _{SP})		
4	56	1		DIVC has been detected and V _{BUS} is being regulated to V _{SP}			
2	EN LEVEL	0	R	DISABLE pin is LOW			
3	EN_LEVEL	1		DISABLE pin is HIGH			
2:0	VSP	100	R/W	DIVC input regulation voltage. See Table 7			
SAFE	TY			Register Address: 06	Default Value=0100 0000 (40h)		
7	Reserved	0	R	Bit disabled and always returns 0 when read back			
6:4	ISAFE	100	R/W	Sets the maximum I _{OCHARGE} value used by the control circuit. See Table 8			
3:0	VSAFE	0000	R/W	Sets the maximum V _{OREG} used by the control circuit. See Table 9			
MONI	TOR			Register Address: 10h (16)			
7	ITERM_CMP		R	ITERM comparator output, 1 w	hen VRSENSE > See Table 5		
6	VBAT_CMP		R	Output of VBAT comparator 1 during charging indicates V _{BA} 1 during HZ_MODE indicates \ 1 during Boost Mode indicated	$V_{\rm BAT} > V_{\rm LOWV}$		
5	LINCHG		R	30 mA linear charger ON			
4	T_120		R	Thermal regulation comparator to 22.1 mV across R _{SENSE}	r; when=1 and T_145=0, the charge current is limited		
3	ICHG		R	0 indicates the I _{OCHARGE} loop is controlling the battery charge current			
2	IBUS		R	0 indicates the IBUS (input current) loop is controlling the battery charge current			
1	VBUS_VALID		R	1 indicates VBUS has passed validation and is capable of charging			
0	CV		R	Indicates the constant-voltage loop (OREG) had been active at least once since the last V _{BUS} plug in O indicates the constant-voltage loop (OREG) had never been reached since the last VBUS plug in or the part is in the Charge Done state with TE=1			

PCB Layout Recommendations

Bypass capacitors should be placed as close to the IC as possible. In particular, the total loop length for CMID should be minimized to reduce overshoot and ringing on the SW, PMID, and VBUS pins. All power and ground pins must be

routed to their bypass capacitors, using top copper whenever possible. Copper area connecting to the IC should be maximized to improve thermal performance if possible.

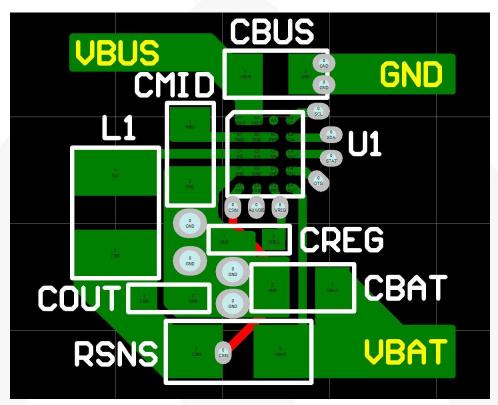
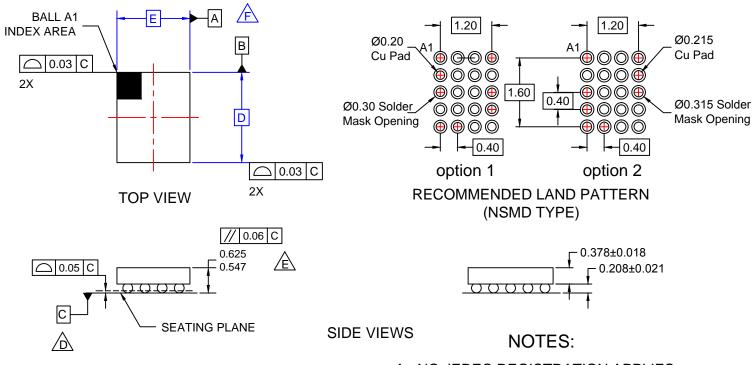


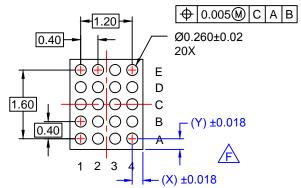
Figure 48. PCB Layout Recommendations

The table below pertains to the MOD information on the following page.

Product-Specific Dimensions

Product	D	E	X	Υ	
FAN54005UCX	1.960 <u>+</u> 0.030 mm	1.870 <u>+</u> 0.030 mm	0.335 mm	0.180 mm	





BOTTOM VIEW

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASMEY14.5M, 2009.
- DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.
- PACKAGE NOMINAL HEIGHT IS 586 MICRONS ±39 MICRONS (547-625 MICRONS).
- FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.
- G. DRAWING FILNAME: MKT-UC020AArev4.



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